

# NTMFS4899NF

## MOSFET – Power, Single, N-Channel, SO-8 FL 30 V, 75 A

### Features

- Integrated Schottky Diode
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- CPU Power Delivery
- DC-DC Converters
- Low Side Switching

MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$  unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	30	V	
Gate-to-Source Voltage		$V_{GS}$	$\pm 20$	V	
Continuous Drain Current $R_{\theta,JA}$ (Note 1)	$T_A = 25^\circ\text{C}$	$I_D$	17.8	A	
	$T_A = 85^\circ\text{C}$		12.9		
Power Dissipation $R_{\theta,JA}$ (Note 1)	$T_A = 25^\circ\text{C}$	$P_D$	2.70	W	
	$T_A = 85^\circ\text{C}$		21		
Continuous Drain Current $R_{\theta,JA} \leq 10$ sec	$T_A = 25^\circ\text{C}$	$I_D$	29.1	A	
	$T_A = 85^\circ\text{C}$		21		
Power Dissipation $R_{\theta,JA}, t \leq 10$ sec	$T_A = 25^\circ\text{C}$	$P_D$	7.18	W	
	$T_A = 85^\circ\text{C}$		21		
Continuous Drain Current $R_{\theta,JA}$ (Note 2)	$T_A = 25^\circ\text{C}$	$I_D$	10.4	A	
	$T_A = 85^\circ\text{C}$		7.5		
Power Dissipation $R_{\theta,JA}$ (Note 2)	$T_A = 25^\circ\text{C}$	$P_D$	0.92	W	
	$T_A = 85^\circ\text{C}$		21		
Continuous Drain Current $R_{\theta,JC}$ (Note 1)	$T_C = 25^\circ\text{C}$	$I_D$	75	A	
	$T_C = 85^\circ\text{C}$		54		
Power Dissipation $R_{\theta,JC}$ (Note 1)	$T_C = 25^\circ\text{C}$	$P_D$	48	W	
	$T_C = 85^\circ\text{C}$		21		
Pulsed Drain Current	$t_p = 10\mu\text{s}$	$T_A = 25^\circ\text{C}$	$I_{DM}$	188	A
Current limited by package		$T_A = 25^\circ\text{C}$	$I_{Dmaxpkg}$	90	A
Operating Junction and Storage Temperature		$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$	
Source Current (Body Diode)		$I_S$	46	A	
Drain to Source $dV/dt$		$dV/dt$	6	V/ns	

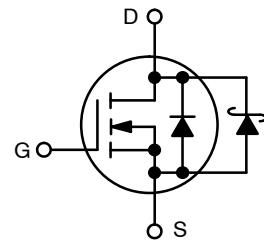
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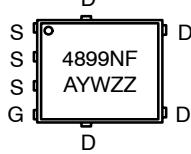
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$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	$I_D$ MAX
30 V	5.0 m $\Omega$ @ 10 V	
	7.5 m $\Omega$ @ 4.5 V	75 A

### N-CHANNEL MOSFET



### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
W = Work Week  
ZZ = Lot Traceability

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTMFS4899NFT1G	SO-8FL (Pb-Free)	1500 / Tape & Reel
NTMFS4899NFT3G	SO-8FL (Pb-Free)	5000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise stated)

Parameter	Symbol	Value	Unit
Single Pulse Drain-to-Source Avalanche Energy (V <sub>DD</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>L</sub> = 41 A <sub>pk</sub> , L = 0.1 mH, R <sub>G</sub> = 25 Ω)	EAS	84	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T <sub>L</sub>	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

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## THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	2.6	$^{\circ}\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	46.3	
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	136.2	
Junction-to-Ambient – $t \leq 10$ sec	$R_{\theta JA}$	17.4	

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size (50 mm<sup>2</sup>, 1 oz Cu).

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0$ V, $I_D = 1.0$ mA		30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(\text{BR})\text{DSS}}/T_J$				27		$\text{mV}/^{\circ}\text{C}$
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{GS}} = 0$ V, $V_{\text{DS}} = 24$ V	$T_J = 25$ $^{\circ}\text{C}$			500	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{DS}} = 0$ V, $V_{\text{GS}} = \pm 20$ V				$\pm 100$	nA

### ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{GS}} = V_{\text{DS}}$ , $I_D = 1.0$ mA		1.5		2.5	V
Negative Threshold Temperature Coefficient	$V_{\text{GS}(\text{TH})}/T_J$				10		$\text{mV}/^{\circ}\text{C}$
Drain-to-Source On Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10$ V	$I_D = 30$ A		3.9	5.0	$\text{m}\Omega$
			$I_D = 15$ A		3.8		
		$V_{\text{GS}} = 4.5$ V	$I_D = 30$ A		6.0	7.5	
			$I_D = 15$ A		5.8		
Forward Transconductance	$g_{\text{FS}}$	$V_{\text{DS}} = 1.5$ V, $I_D = 15$ A			57		S

### CHARGES AND CAPACITANCES

Input Capacitance	$C_{\text{ISS}}$	$V_{\text{GS}} = 0$ V, $f = 1$ MHz, $V_{\text{DS}} = 12$ V		1600		pF
Output Capacitance	$C_{\text{OSS}}$			360		
Reverse Transfer Capacitance	$C_{\text{RSS}}$			165		
Total Gate Charge	$Q_{\text{G}(\text{TOT})}$	$V_{\text{GS}} = 4.5$ V, $V_{\text{DS}} = 15$ V; $I_D = 30$ A		12.2		nC
Threshold Gate Charge	$Q_{\text{G}(\text{TH})}$			1.6		
Gate-to-Source Charge	$Q_{\text{GS}}$			4.6		
Gate-to-Drain Charge	$Q_{\text{GD}}$			4.6		
Total Gate Charge	$Q_{\text{G}(\text{TOT})}$	$V_{\text{GS}} = 10$ V, $V_{\text{DS}} = 15$ V, $I_D = 30$ A		25		nC

### SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{\text{d}(\text{ON})}$	$V_{\text{GS}} = 4.5$ V, $V_{\text{DS}} = 15$ V, $I_D = 15$ A, $R_G = 3.0$ $\Omega$		12.6		ns
Rise Time	$t_r$			20.3		
Turn-Off Delay Time	$t_{\text{d}(\text{OFF})}$			20		
Fall Time	$t_f$			4.2		

3. Pulse Test: pulse width  $\leq 300$   $\mu\text{s}$ , duty cycle  $\leq 2\%$ .
4. Switching characteristics are independent of operating junction temperatures.

# NTMFS4899NF

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A, R <sub>G</sub> = 3.0 Ω		8.8		ns
Rise Time	t <sub>r</sub>			18.5		
Turn-Off Delay Time	t <sub>d(OFF)</sub>			25.9		
Fall Time	t <sub>f</sub>			2.5		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 2.0 A	T <sub>J</sub> = 25°C		0.45	0.70	V
			T <sub>J</sub> = 125°C		0.43		
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs, I <sub>S</sub> = 30 A			19		ns
Charge Time	t <sub>a</sub>				9.2		
Discharge Time	t <sub>b</sub>				9.8		
Reverse Recovery Charge	Q <sub>RR</sub>				5.7		nC

### PACKAGE PARASITIC VALUES

Source Inductance	L <sub>S</sub>	T <sub>A</sub> = 25°C		0.38		nH
Drain Inductance	L <sub>D</sub>			0.005		
Gate Inductance	L <sub>G</sub>			1.84		
Gate Resistance	R <sub>G</sub>			1.5	2.4	Ω

3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

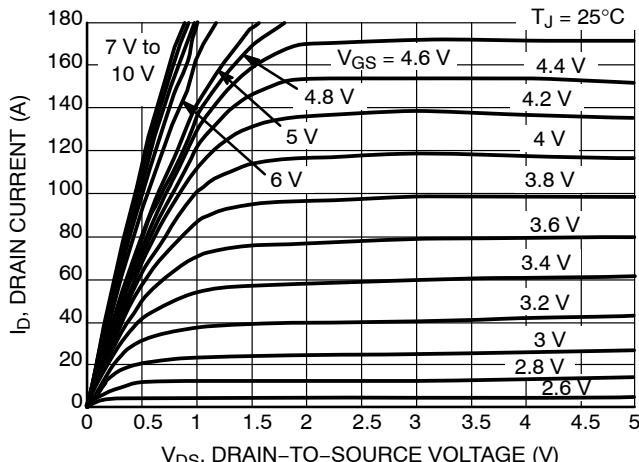


Figure 1. On-Region Characteristics

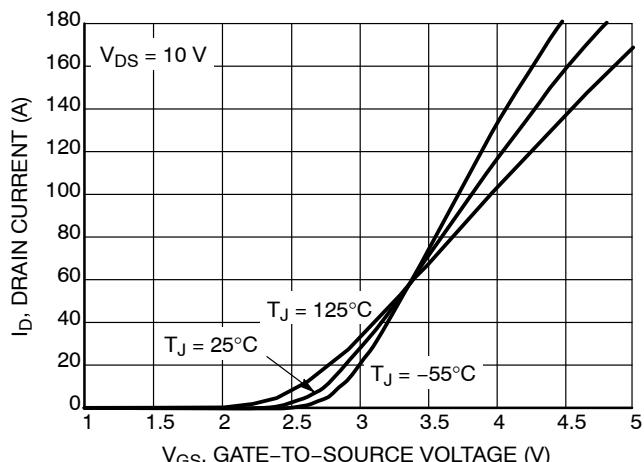


Figure 2. Transfer Characteristics

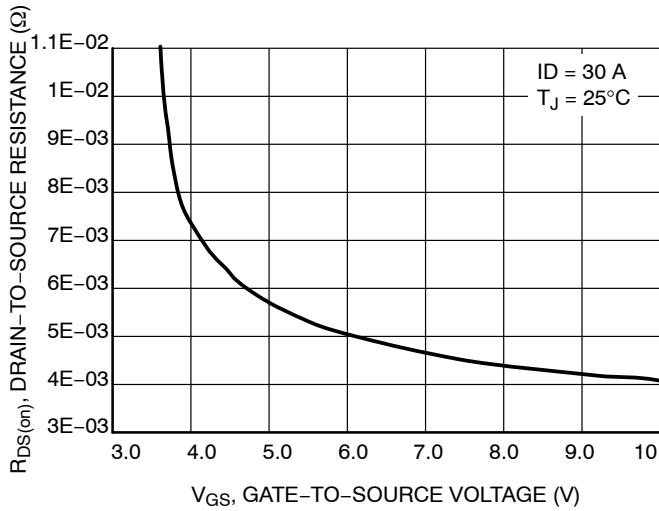


Figure 3. On-Region versus  $V_{GS}$

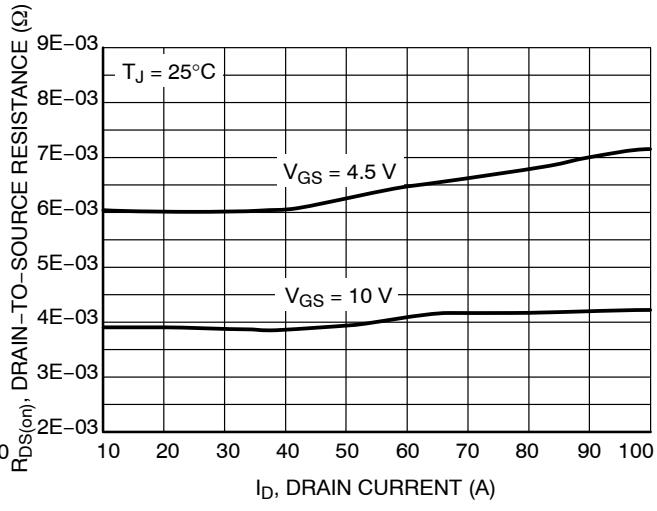


Figure 4. On-Resistance versus Drain Current and Gate Voltage

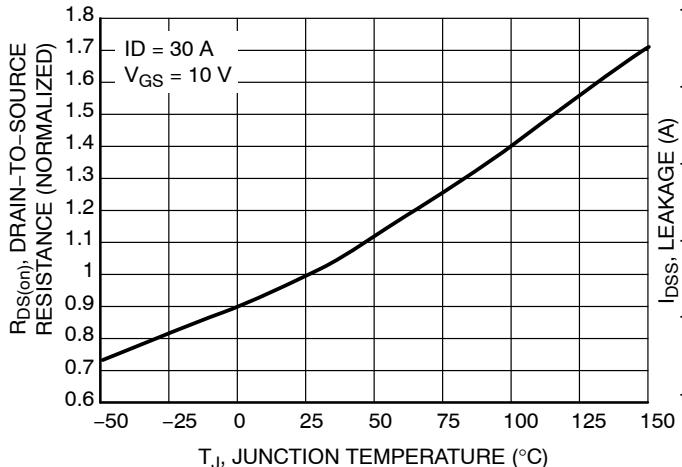


Figure 5. On-Resistance Variation with Temperature

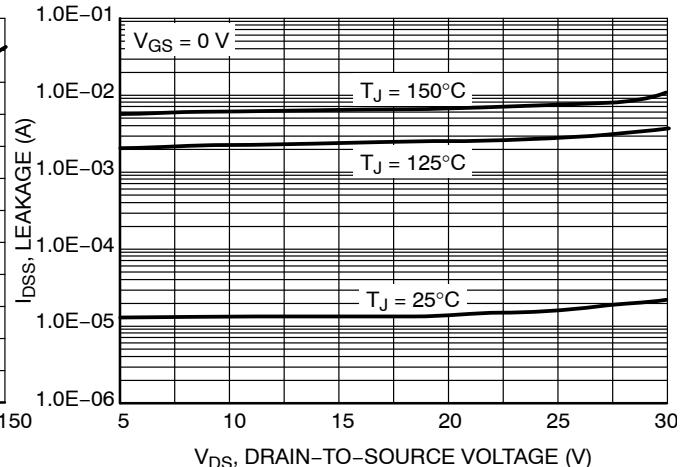
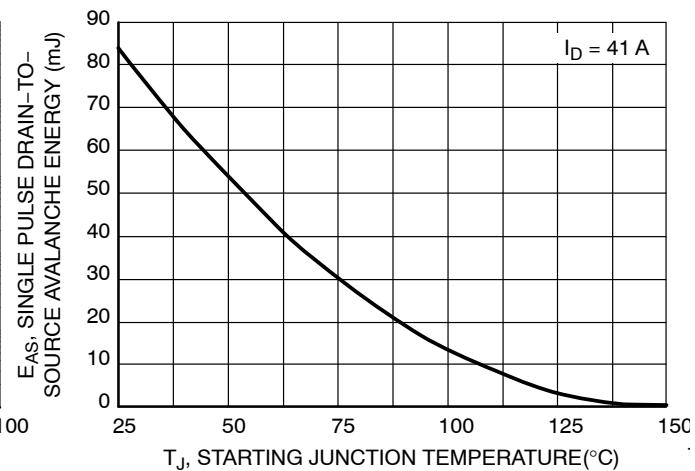
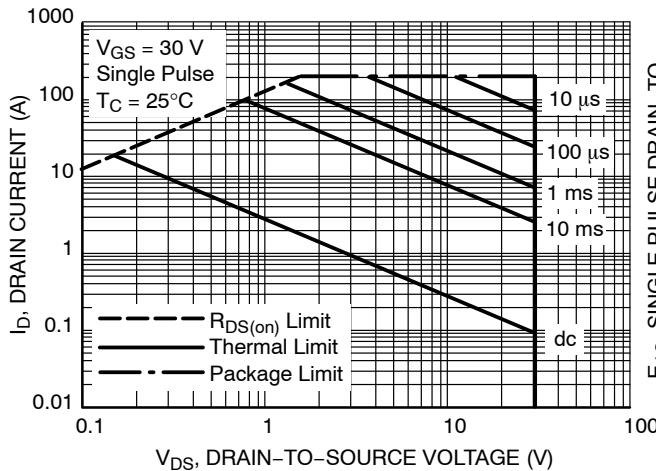
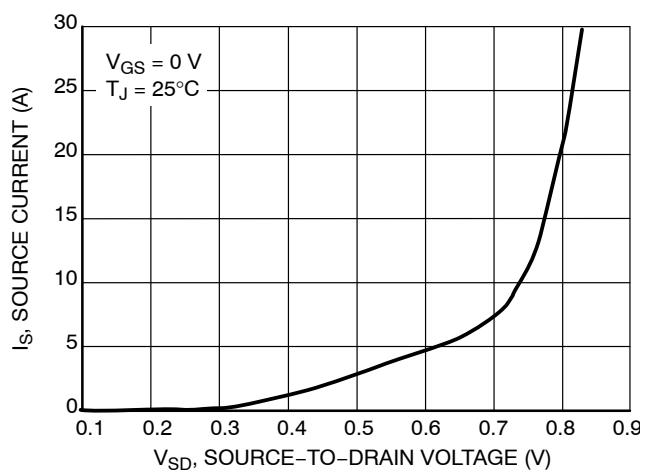
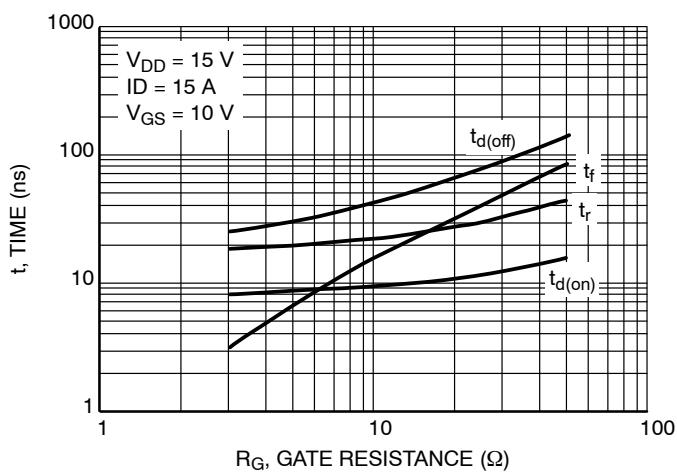
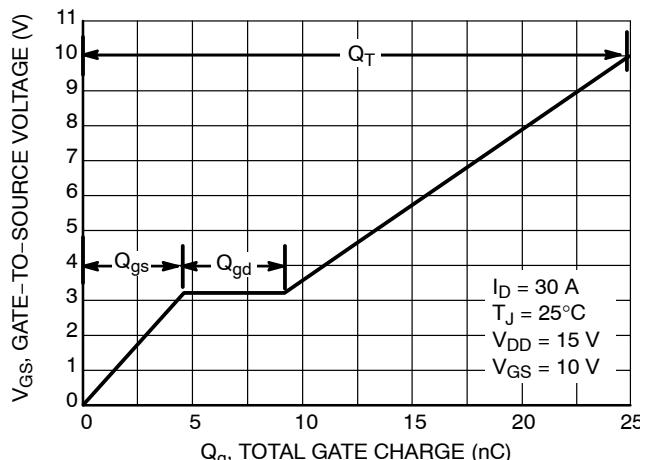
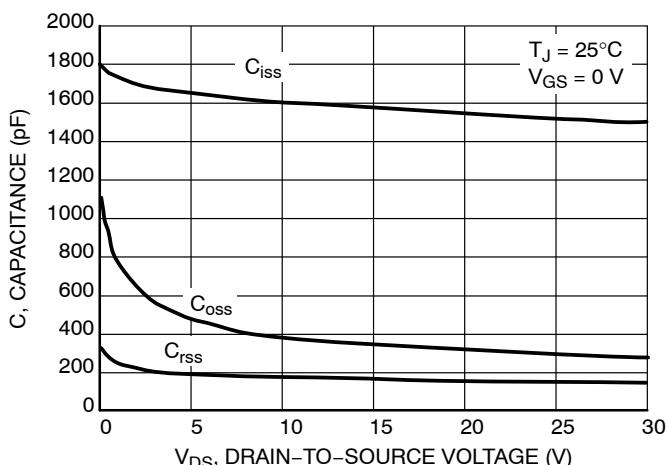


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS



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## TYPICAL CHARACTERISTICS

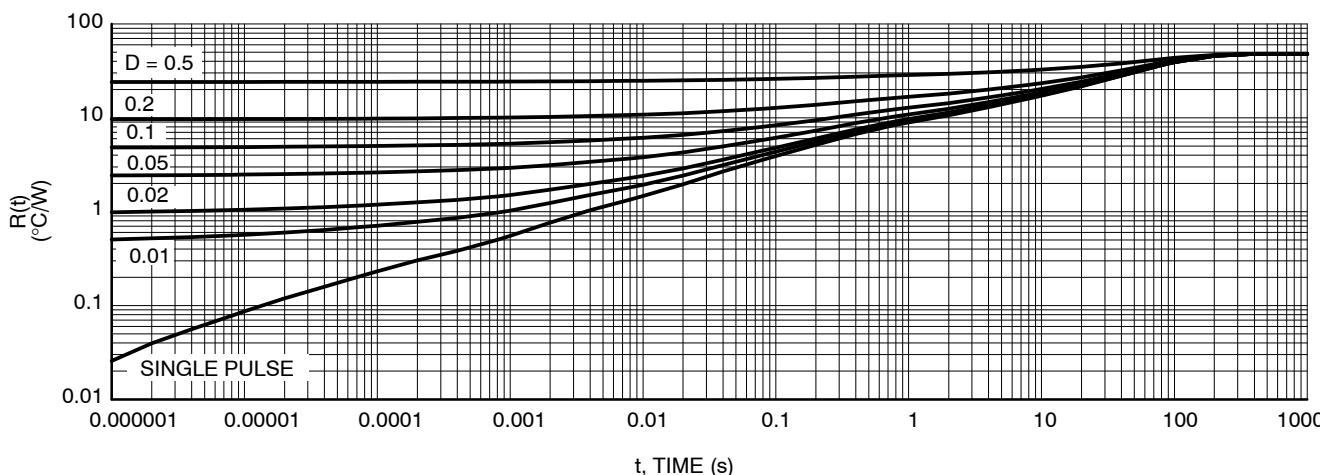
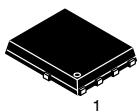


Figure 13. Thermal Response



SCALE 2:1

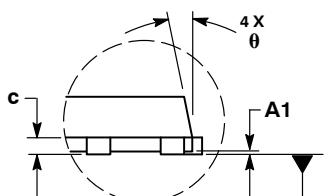
DFN5 5x6, 1.27P  
(SO-8FL)  
CASE 488AA  
ISSUE N

DATE 25 JUN 2018

## NOTES:

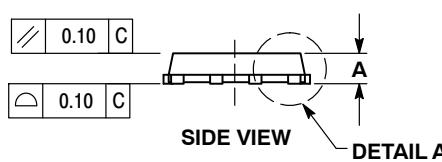
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	----	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °	----	12 °

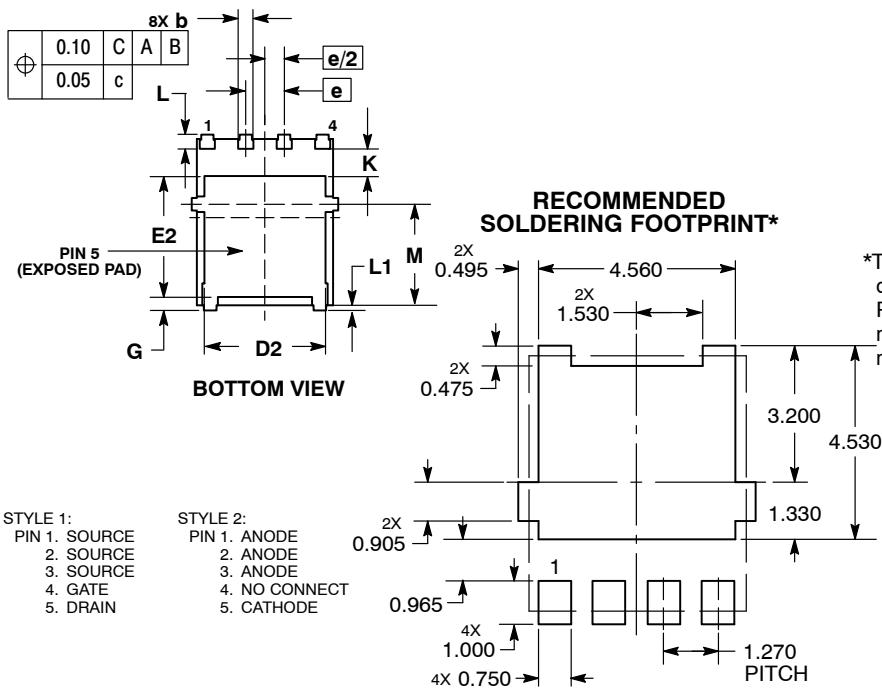


DETAIL A

SEATING PLANE



DETAIL A



STYLE 1:  
PIN 1. SOURCE  
2. SOURCE  
3. SOURCE  
4. GATE  
5. DRAIN

STYLE 2:  
PIN 1. ANODE  
2. ANODE  
3. ANODE  
4. NO CONNECT  
5. CATHODE

DIMENSIONS: MILLIMETERS

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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